



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: MINETANI, Keiji

Group Art Unit: 2822

Serial No.: 09/893,477

Examiner: M. LEWIS

Filed: June 29, 2001

P.T.O. Confirmation No.: 5295

FOR: COMPOUND SEMICONDUCTOR DEVICE HAVING A MESFET THAT RAISES
THE MAXIMUM MUTUAL CONDUCTANCE AND CHANGES THE MUTUAL
CONDUCTANCE

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

May 29, 2003

Sir:

In response to the Office Action dated January 29, 2003, extended to May 29, 2003 by a
one-month Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS:

AMEND claim 1 to read as follows:

1. (Thrice amended) A compound semiconductor device comprising:
- a substrate formed of a first compound semiconductor;
 - a buffer layer formed on the substrate;
 - a graded channel layer formed on the buffer layer, said graded channel layer composed of a second compound semiconductor layer doped with an impurity of which one constituent element of said second compound semiconductor layer has a peak distribution in the inside of said graded channel layer in a thickness direction, thereby an energy band gap of the graded channel layer is

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